



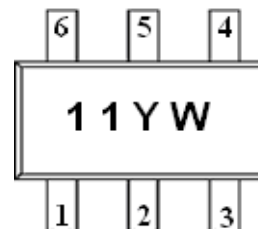
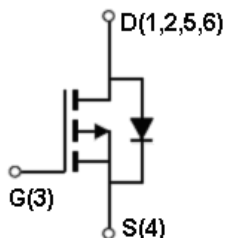
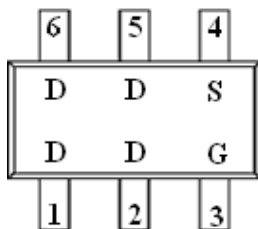
General Description

AFP7611, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge. These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -20V/-3.0A, $R_{DS(ON)}=110m\Omega@V_{GS}=-4.5V$
- -20V/-2.4A, $R_{DS(ON)}=135m\Omega@V_{GS}=-2.5V$
- -20V/-2.0A, $R_{DS(ON)}=180m\Omega@V_{GS}=-1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-363 package design

Pin Description (SOT-363)



Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Net Working System

Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP7611S36RG	11YW	SOT-363	Tape & Reel	3000 EA

- ※ 11 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP7611S36RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

($T_A=25^\circ\text{C}$ Unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	± 12	V	
Continuous Drain Current($T_J=150^\circ\text{C}$)	I_D	$T_A=25^\circ\text{C}$	-3.0	A
		$T_A=70^\circ\text{C}$	-2.0	
Pulsed Drain Current	I_{DM}	-8	A	
Continuous Source Current(Diode Conduction)	I_S	-1.4	A	
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	1.5	W
		$T_A=70^\circ\text{C}$	0.8	
Operating Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature Range	T_{STG}	-55/150	$^\circ\text{C}$	
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ\text{C/W}$	

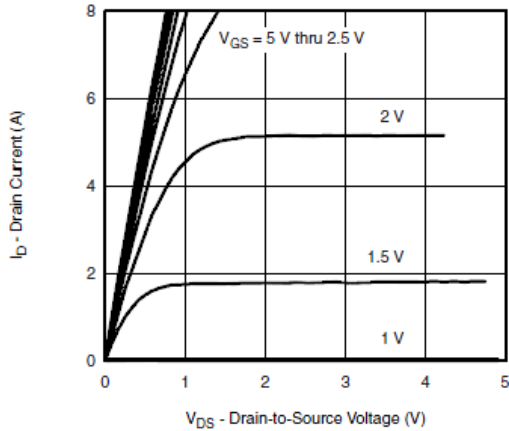
Electrical Characteristics

($T_A=25^\circ\text{C}$ Unless otherwise noted)

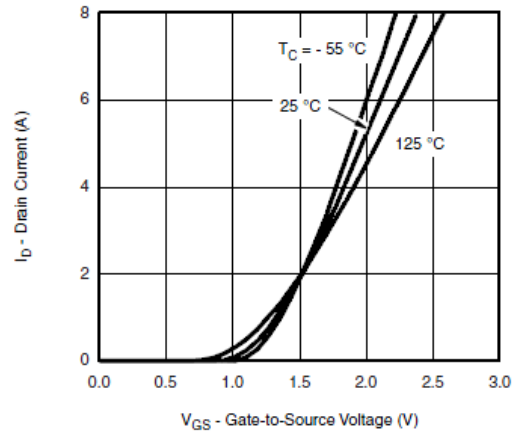
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu\text{A}$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.5	-0.7	-1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0V$			-1	uA
		$V_{DS}=-16V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			-30	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-4.5V$	-4			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-3.0A$		95	110	m Ω
		$V_{GS}=-2.5V, I_D=-2.4A$		115	135	
		$V_{GS}=-1.8V, I_D=-2.0A$		155	180	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-2.8A$		6.5		S
Diode Forward Voltage	V_{SD}	$I_S=-1.25A, V_{GS}=0V$		-0.75	-1.3	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V$ $I_D=-2.9A$		5.8	10	nC
Gate-Source Charge	Q_{gs}			1.1		
Gate-Drain Charge	Q_{gd}			1.1		
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V$ $f=1\text{MHz}$		550	750	pF
Output Capacitance	C_{oss}			90		
Reverse Transfer Capacitance	C_{rss}			70		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=10\Omega$ $I_D=-1.0A, V_{GEN}=-4.5V$ $R_G=6\Omega$		1.0	2.0	us
	t_r			2.0	3.0	
Turn-Off Time	$t_{d(off)}$			4.0	6.0	
	t_f			4.0	6.0	



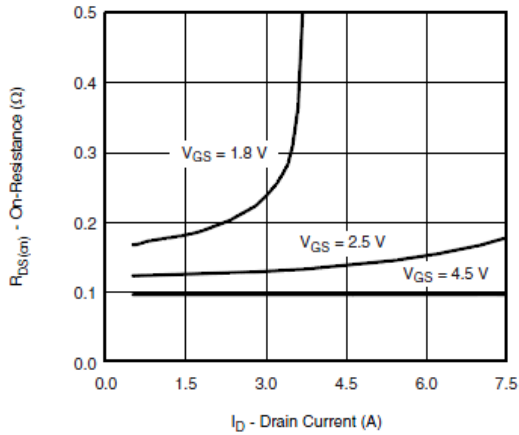
Typical Characteristics



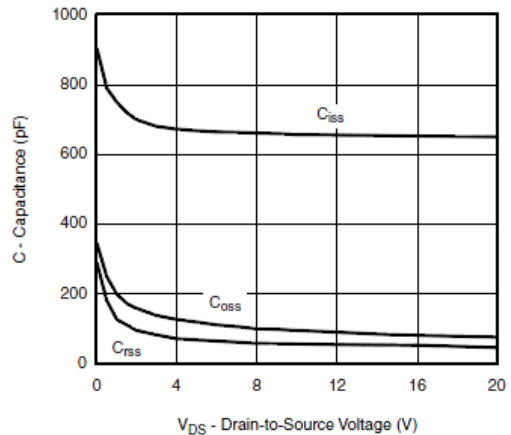
Output Characteristics



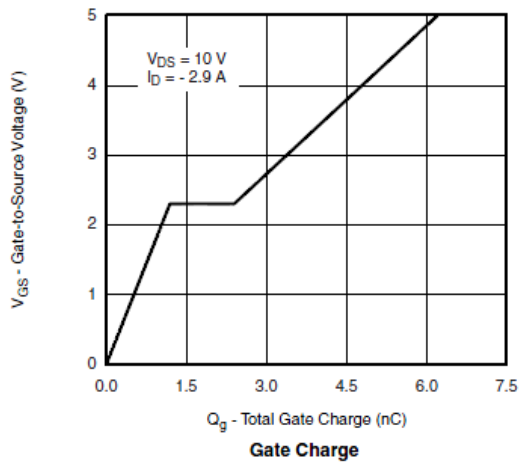
Transfer Characteristics



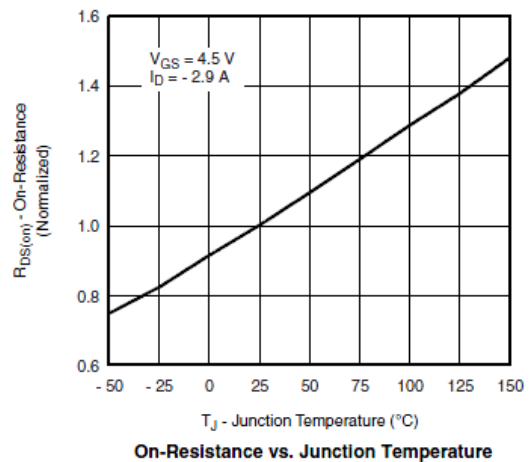
On-Resistance vs. Drain Current



Capacitance



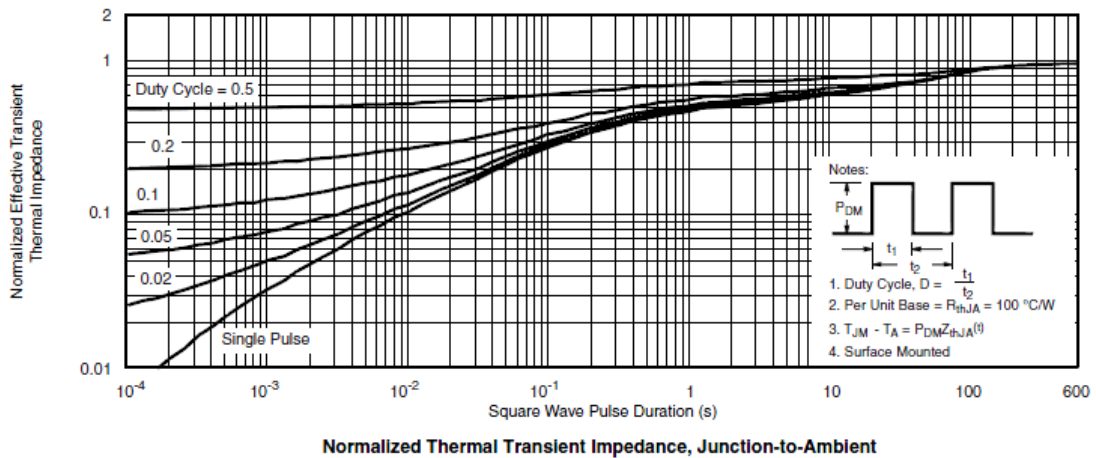
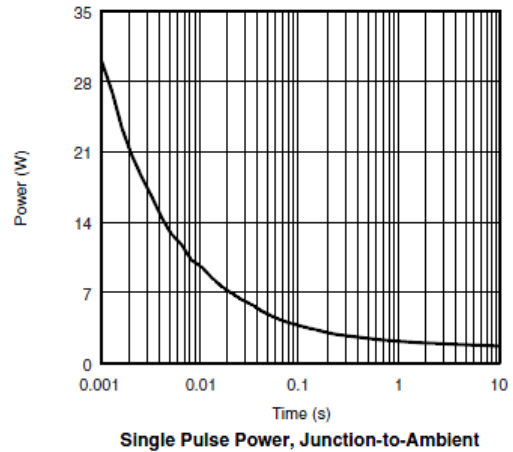
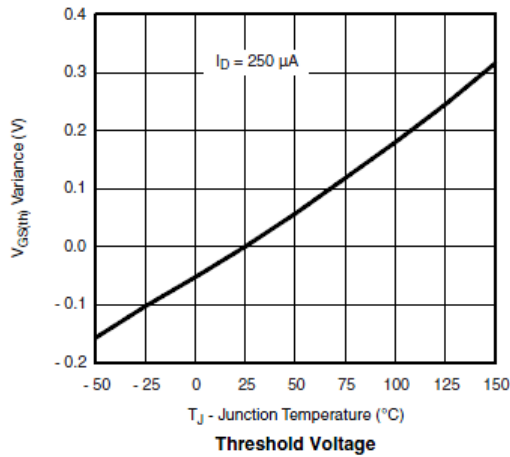
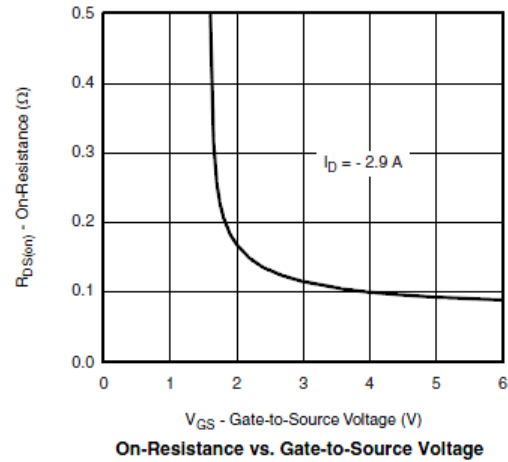
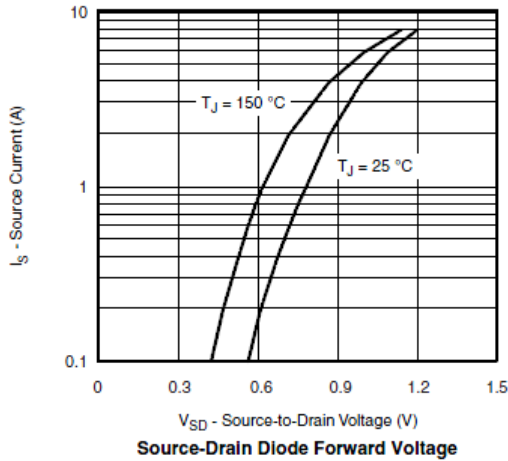
Gate Charge



On-Resistance vs. Junction Temperature



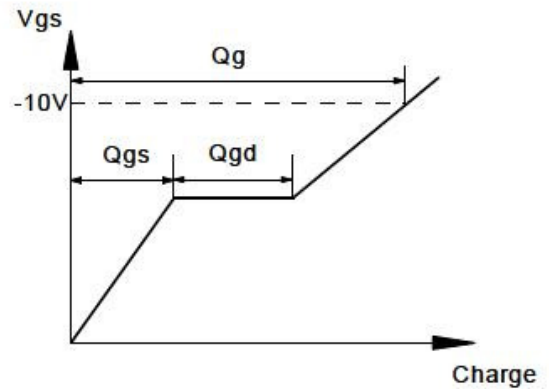
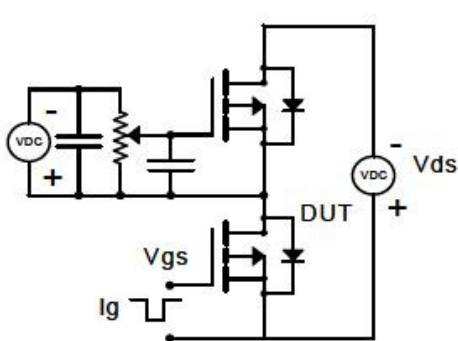
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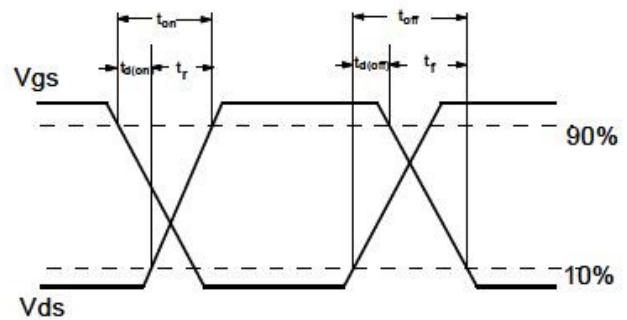
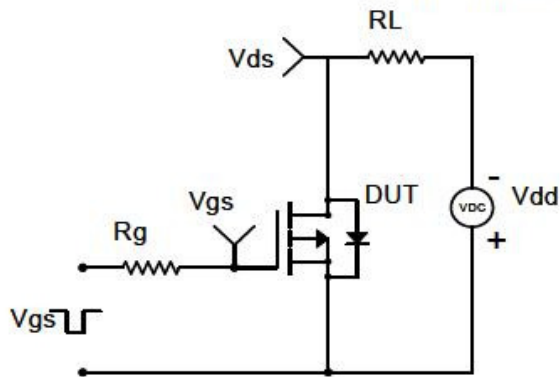


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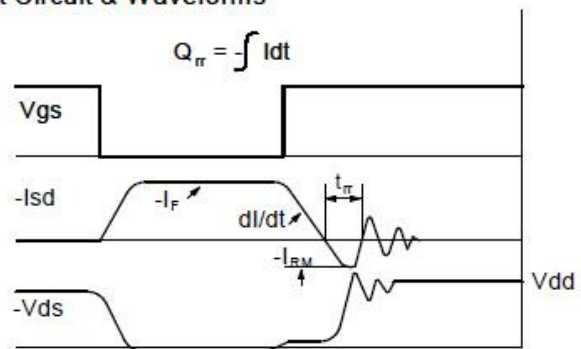
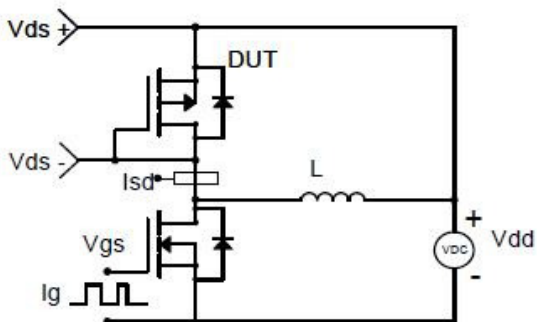
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

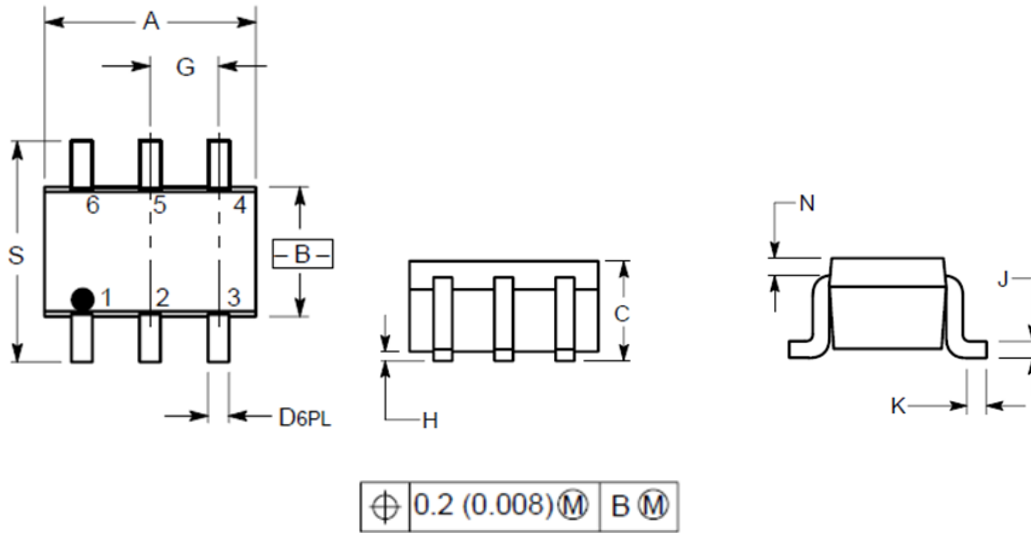


Diode Recovery Test Circuit & Waveforms





Package Information (SOT-363)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

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